ABSTRACT

MOSFET WITH ELECTROSTATIC DISCHARGE PROTECTION STRUCTURE AND METHOD OF FABRICATION

A semiconductor circuit comprises a semiconductor substrate, a semiconductor device having a drain region disposed in the substrate, and a reverse doped region laterally adjacent and laterally contacting the drain region wherein the reverse doped region has an opposite doping type from that of the drain region and a dopant concentration higher than that of the semiconductor substrate, the reverse doped region and the drain operable to form a p-n junction.

Fig. 1a

